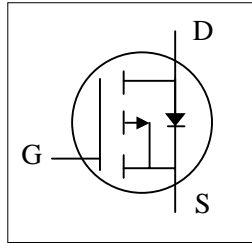
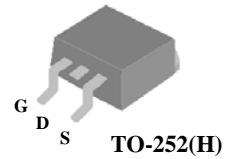




- ▼ 100% UIS Test
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	-20V
$R_{DS(ON)}$	150m $\Omega$
$I_D$	-8.3A



**Description**

AP2P150 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance.

**Absolute Maximum Ratings @ $T_J=25^\circ\text{C}$ (unless otherwise specified)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_C=25^\circ\text{C}$	Drain Current, $V_{GS}$ @ 4.5V	-8.3	A
$I_D @ T_C=100^\circ\text{C}$	Drain Current, $V_{GS}$ @ 4.5V	-5.3	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-24	A
$P_D @ T_C=25^\circ\text{C}$	Total Power Dissipation	15.6	W
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	2	W
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	1.25	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

**Thermal Data**

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	8	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>4</sup>	62.5	$^\circ\text{C/W}$



# AP2P150H

## Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-4.5V, I_D=-4A$	-	-	150	$m\Omega$
		$V_{GS}=-2.5V, I_D=-2A$	-	-	250	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-	-1.25	V
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V, I_D=-4A$	-	5	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-16V, V_{GS}=0V$	-	-	-10	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge	$I_D=-4A$	-	4.7	7.5	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=-16V$	-	1.2	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	1.6	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=-10V$	-	7	-	ns
$t_r$	Rise Time	$I_D=-4A$	-	30	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	13	-	ns
$t_f$	Fall Time	$V_{GS}=-5V$	-	4	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	365	584	pF
$C_{oss}$	Output Capacitance	$V_{DS}=-10V$	-	70	-	pF
$C_{riss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	55	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=-4A, V_{GS}=0V$	-	-	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_S=-4A, V_{GS}=0V,$	-	21	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=-100A/\mu s$	-	10	-	nC

### Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Starting  $T_j=25^{\circ}\text{C}$ ,  $V_{DD}=-20V$ ,  $L=0.1\text{mH}$ ,  $R_G=25\Omega$ ,  $V_{GS}=-10V$
4. Surface mounted on  $1\text{ in}^2$  copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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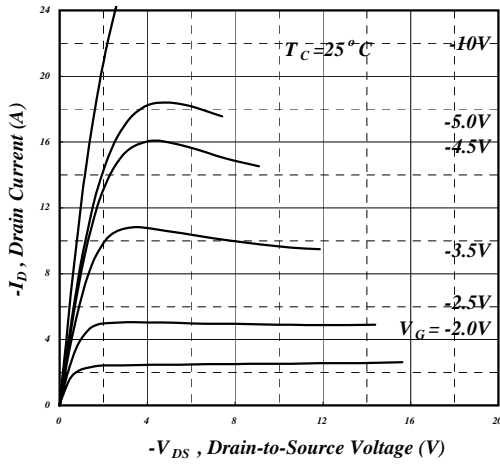


Fig 1. Typical Output Characteristics

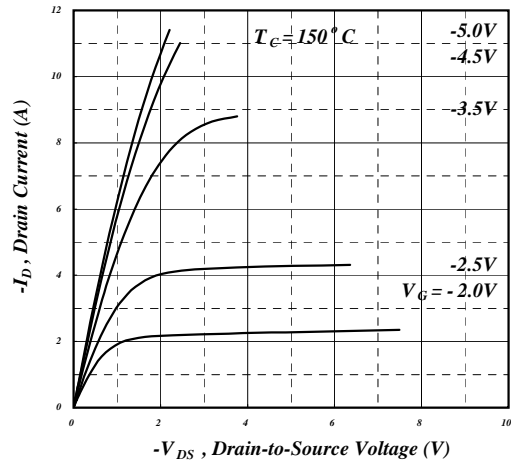


Fig 2. Typical Output Characteristics

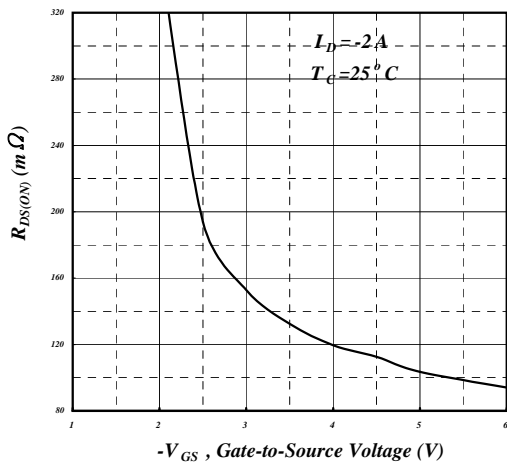


Fig 3. On-Resistance v.s. Gate Voltage

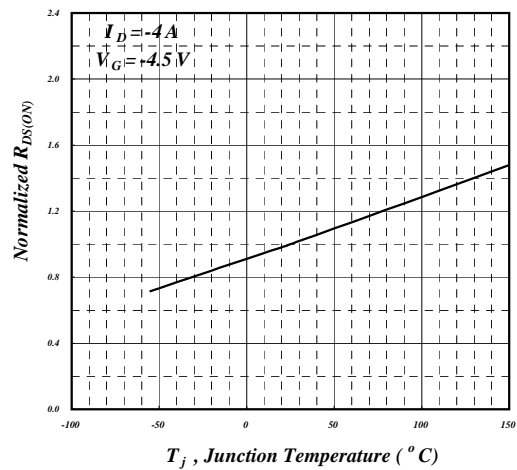


Fig 4. Normalized On-Resistance v.s. Junction Temperature

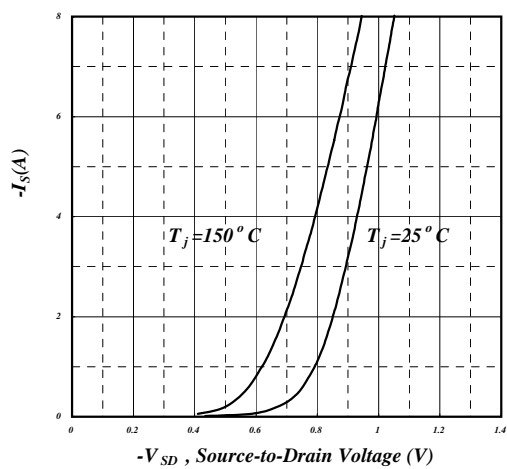


Fig 5. Forward Characteristic of Reverse Diode

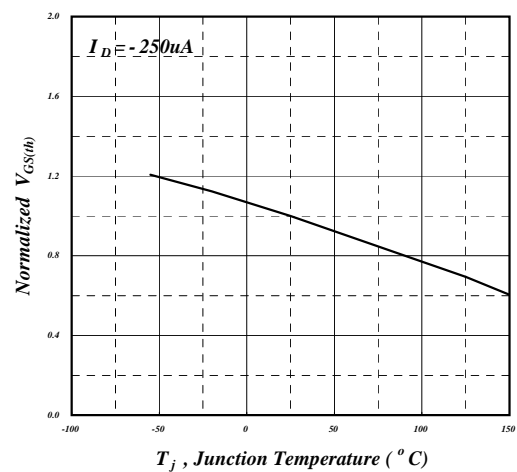
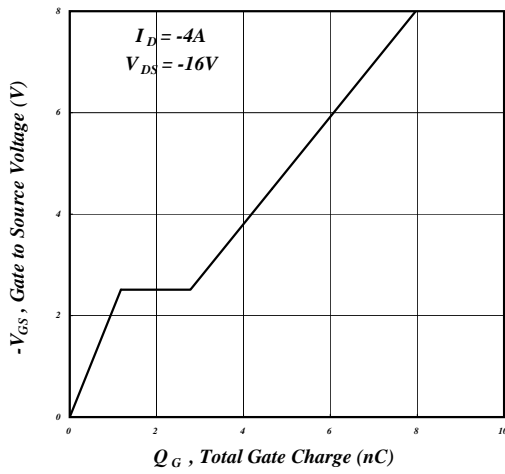
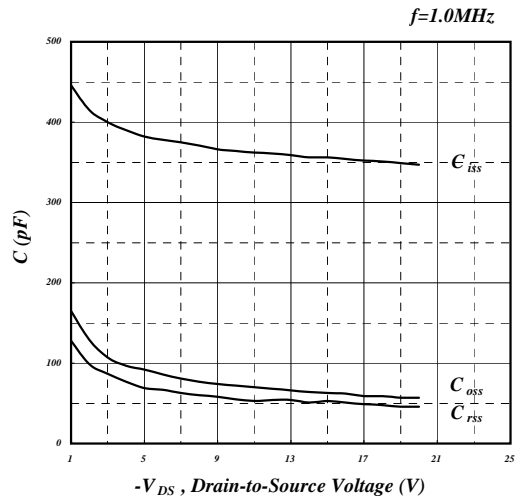


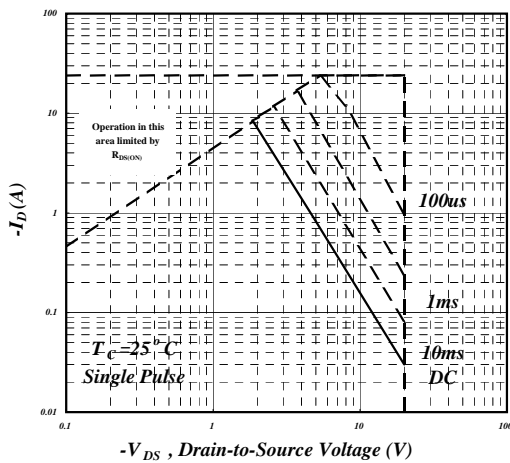
Fig 6. Gate Threshold Voltage v.s. Junction Temperature



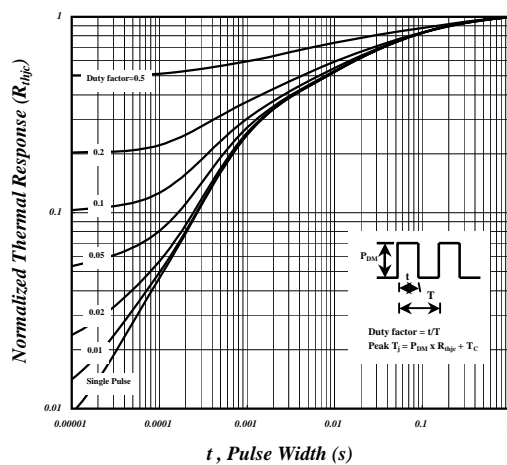
**Fig 7. Gate Charge Characteristics**



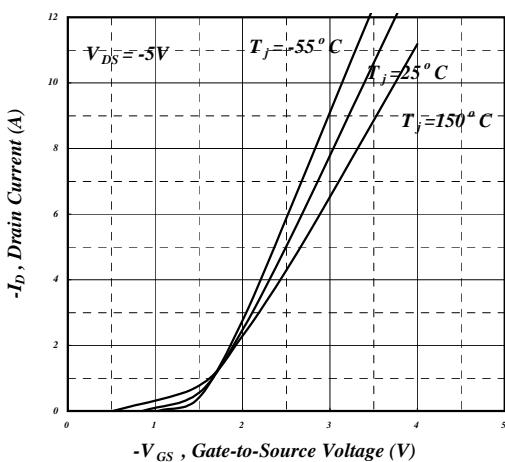
**Fig 8. Typical Capacitance Characteristics**



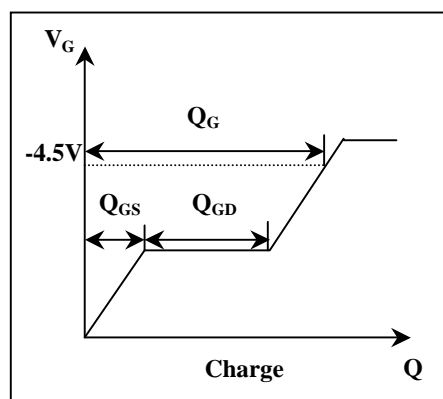
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Transfer Characteristics**



**Fig 12. Gate Charge Waveform**

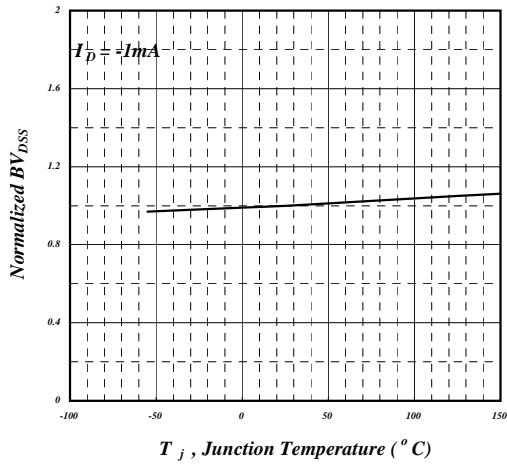


Fig 13. Normalized  $BV_{DSS}$  v.s. Junction Temperature

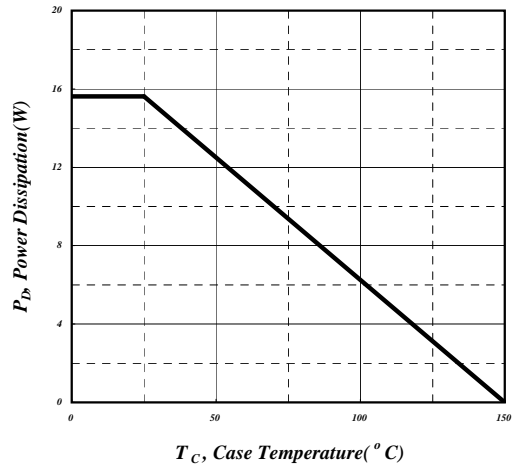


Fig 14. Total Power Dissipation

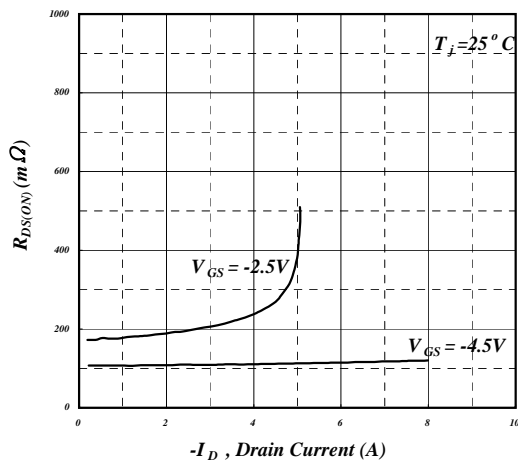


Fig 15. Typ. Drain-Source on State Resistance

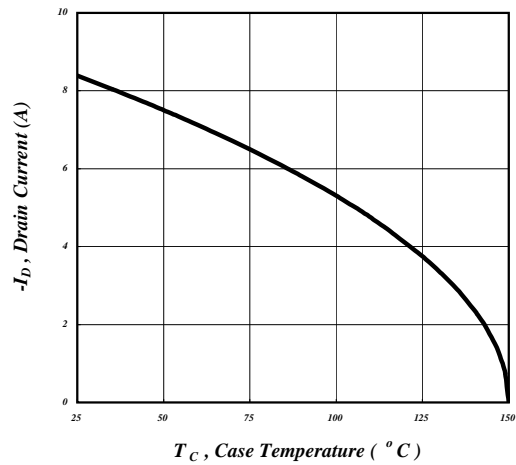


Fig 16. Drain Current v.s. Case Temperature



# AP2P150H

## MARKING INFORMATION

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